NEC

# MOS FIELD EFFECT POWER TRANSISTORS
# 2SJ326, 2SJ326-Z

## SWITCHING
## P-CHANNEL POWER MOS FET
## INDUSTRIAL USE

### DESCRIPTION

The 2SJ326 is P-channel MOS Field Effect Transistor designed for solenoid, motor and lamp driver.

### FEATURES

- Low On-state Resistance
  $R_{DS(on)}$ = 0.28 Ω TYP. ($V_{GS}$ = −10 V, $I_D$ = −1 A)
  $R_{DS(on)}$ = 0.50 Ω TYP. ($V_{GS}$ = −4 V, $I_D$ = −0.8 A)
- Low $C_{iss}$ $C_{iss}$ = 320 pF TYP.
- Built-in G-S Gate Protection Diode

### QUALITY GRADE

Standard

Please refer to "Quality grade on NEC Semiconductor Devices" (Document number IEI-1209) published by NEC Corporation to know the specification of quality grade on the devices and its recommended applications.

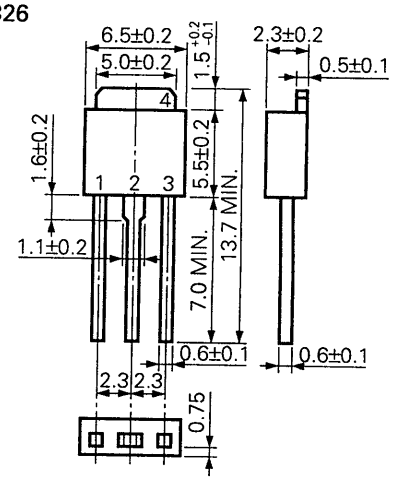
### ABSOLUTE MAXIMUM RATINGS ($T_a$ = 25 °C)

| | | | |
|---|---|---|---|
| Drain to Source Voltage | $V_{DSS}$ | −60 | V |
| Gate to Source Voltage (AC) | $V_{GSS}$ | ∓20 | V |
| Gate to Source Voltage (DC) | $V_{GSS}$ | −20, +10 | V |
| Drain Current (DC) | $I_{D(DC)}$ | ∓2.0 | A |
| Drain Current (pulse) | $I_{D(pulse)}$* | ∓8.0 | A |
| Total Power Dissipation ($T_C$ = 25 °C) | $P_{T1}$ | 20 | W |
| Total Power Dissipation ($T_a$ = 25 °C) | $P_{T2}$ | 1.0 | W |
| Channel Temperature | $T_{ch}$ | 150 | °C |
| Storage Temperature | $T_{stg}$ | −55 to +150 | °C |

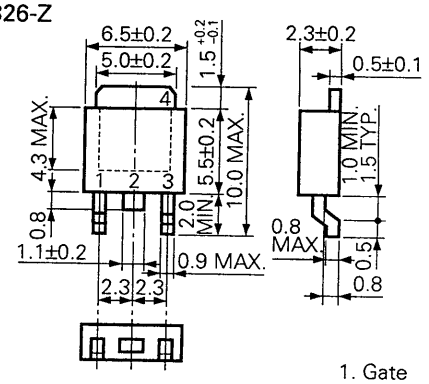
* PW ≦ 10 μs, Duty Cycle ≦ 1 %

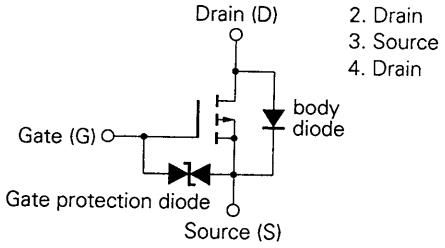
### PACKAGE DIMENSIONS
in millimeters

2SJ326




2SJ326-Z




1. Gate
2. Drain
3. Source
4. Drain

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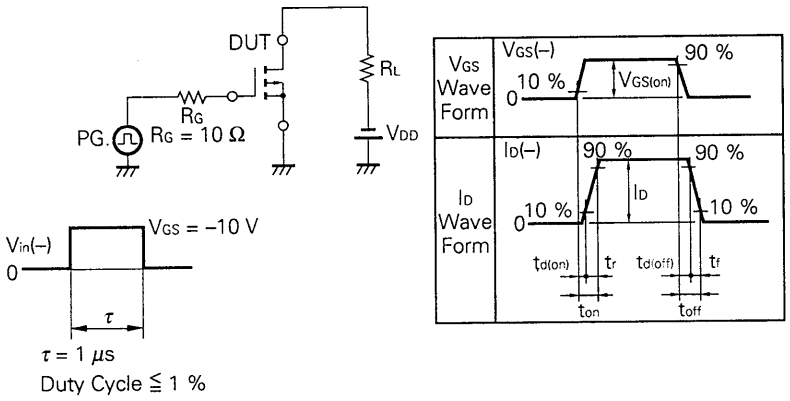
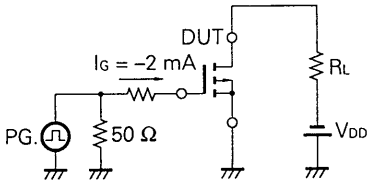
## ELECTRICAL CHARACTERISTICS ($T_a$ = 25 °C)

| CHARACTERISTIC | SYMBOL | MIN. | TYP. | MAX. | UNIT | TEST CONDITIONS |
|---|---|---|---|---|---|---|
| Drain to Source On-state Resistance | $R_{DS(on)}$ | | 0.28 | 0.37 | Ω | $V_{GS}$ = −10 V, $I_D$ = −1.0 A |
| Drain to Source On-state Resistance | $R_{DS(on)}$ | | 0.50 | 0.68 | Ω | $V_{GS}$ = −4 V, $I_D$ = −0.8 A |
| Gate to Source Cutoff Voltage | $V_{GS(off)}$ | −1.0 | −1.5 | −2.0 | V | $V_{DS}$ = −10 V, $I_D$ = −1 mA |
| Forward Transfer Admittance | $\|y_{fs}\|$ | 1.0 | 1.8 | | S | $V_{DS}$ = −10 V, $I_D$ = −1.0 A |
| Drain Leakage Current | $I_{DSS}$ | | | −10 | μA | $V_{DS}$ = −60 V, $V_{GS}$ = 0 |
| Gate to Source Leakage Current | $I_{GSS}$ | | | ∓10 | μA | $V_{GS}$ = ∓16 V, $V_{DS}$ = 0 |
| Input Capacitance | $C_{iss}$ | | 320 | | pF | $V_{DS}$ = −10 V<br>$V_{GS}$ = 0<br>f = 1 MHz |
| Output Capacitance | $C_{oss}$ | | 220 | | pF | |
| Reverse Transfer Capacitance | $C_{rss}$ | | 75 | | pF | |
| Turn-On Delay Time | $t_{d(on)}$ | | 5 | | ns | $V_{GS(on)}$ = −10 V<br>$V_{DD}$ = −30 V<br>$I_D$ = −1.0 A, $R_G$ = 10 Ω<br>$R_L$ = 30 Ω |
| Rise Time | $t_r$ | | 15 | | ns | |
| Turn-Off Delay Time | $t_{d(off)}$ | | 40 | | ns | |
| Fall Time | $t_f$ | | 25 | | ns | |
| Total Gate Charge | $Q_G$ | | 12 | | nC | $V_{GS}$ = −10 V<br>$I_D$ = −2.0 A<br>$V_{DD}$ = −48 V |
| Gate to Source Charge | $Q_{GS}$ | | 1 | | nC | |
| Gate to Drain Charge | $Q_{GD}$ | | 5 | | nC | |
| Body Diode Forward Voltage | $V_F$ | | 0.9 | | V | $I_F$ = 2.0 A, $V_{GS}$ = 0 |
| ESD | $V_{ESD}$ | | ±130 | | V | C = 200 pF, R = 0, Single Pulse |
| Reverse Recovery Time | $t_{rr}$ | | 72 | | ns | $I_F$ = 2.0 A, $V_{GS}$ = 0<br>di/dt = 50 A/μs |
| Reverse Recovery Charge | $Q_{rr}$ | | 30 | | nC | |

### Test Circuit 1: Switching Time

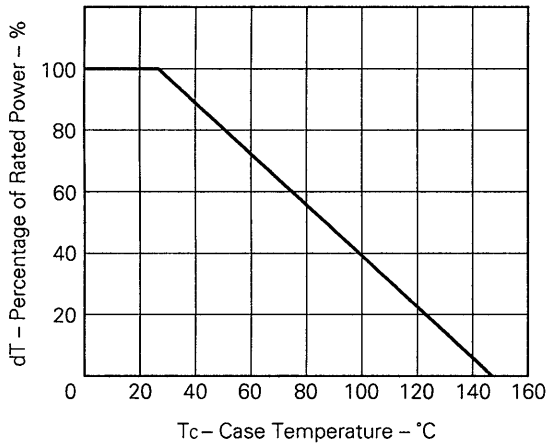



### Test Circuit 2: Gate Charge

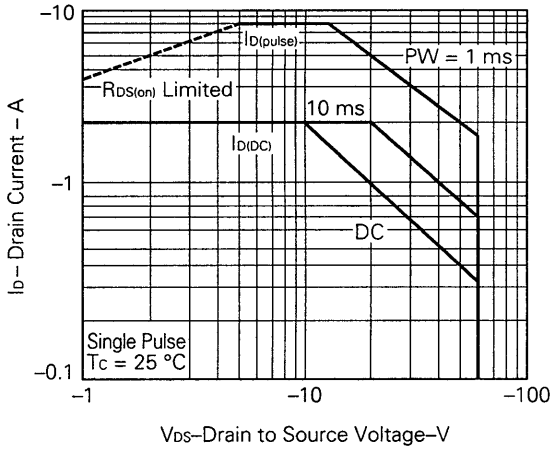


## ELECTRICAL CHARACTERISTICS ($T_a$ = 25 °C)

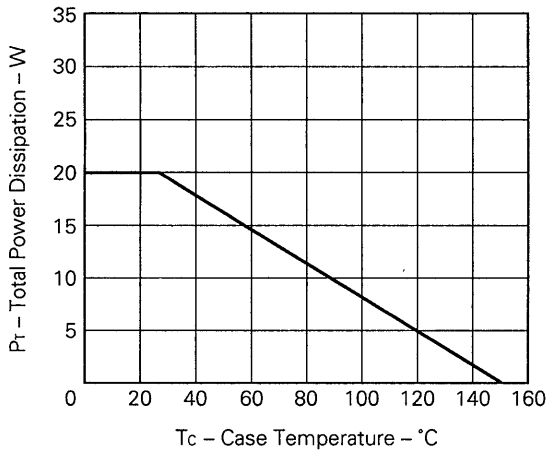
DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA



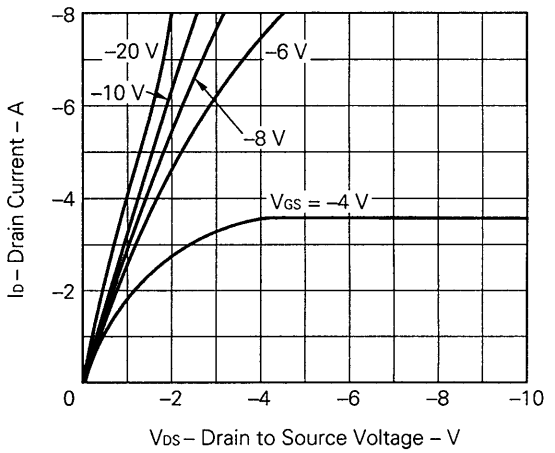

FORWARD BIAS SAFE OPERATING AREA



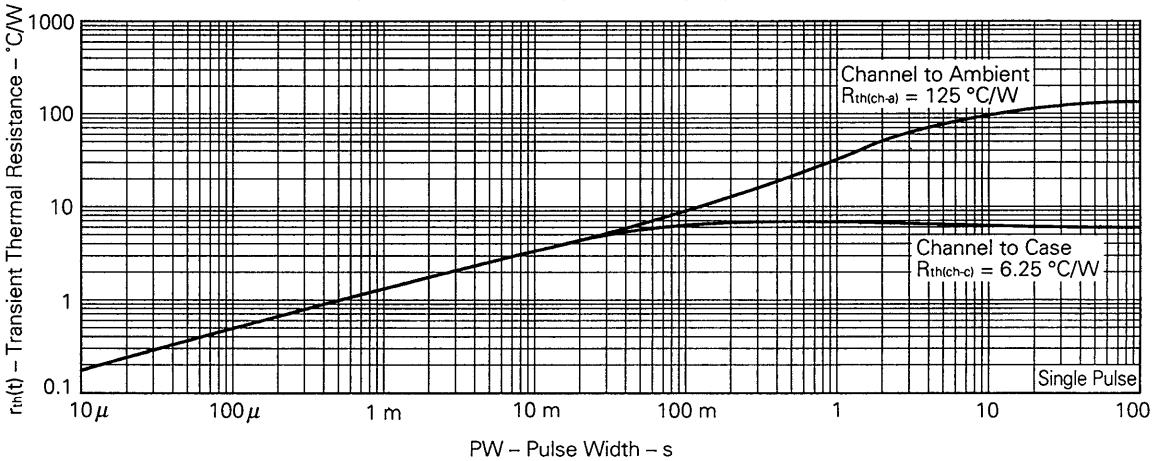

TOTAL POWER DISSIPATION vs. CASE TEMPERATURE



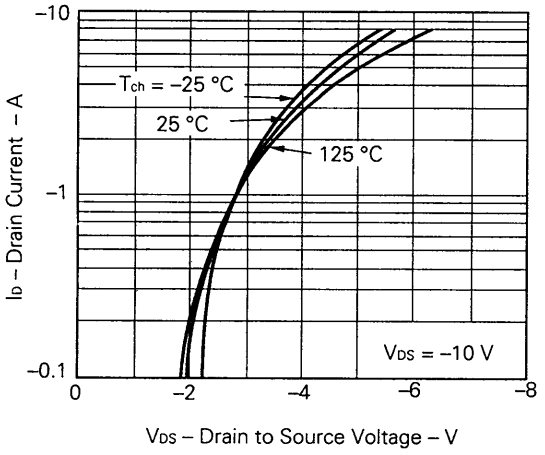

DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



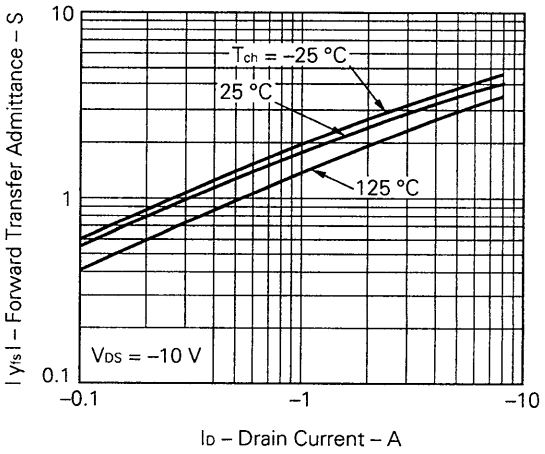

TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



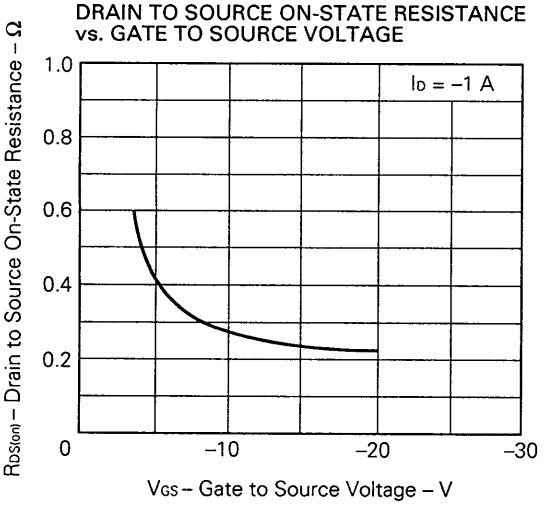
TRANSFER CHARACTERISTICS



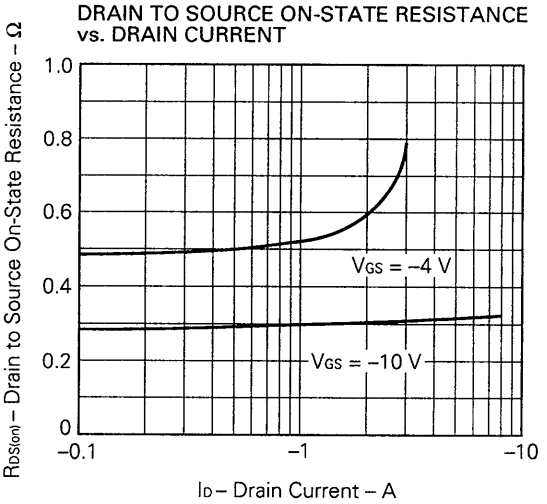

FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



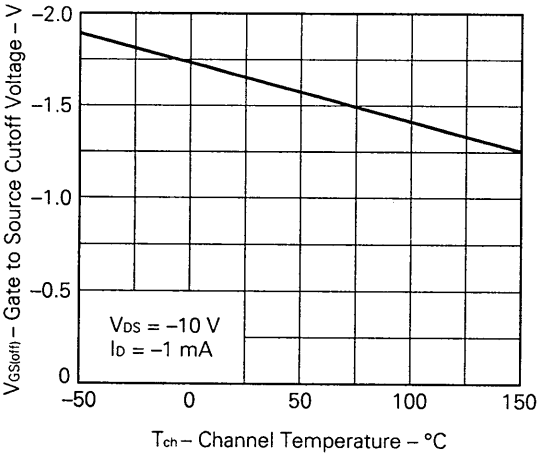

DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



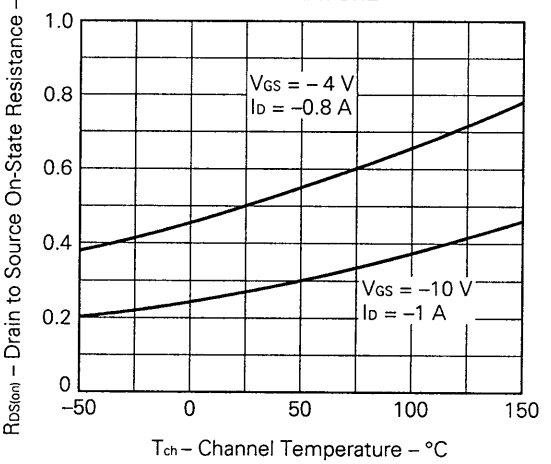

DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



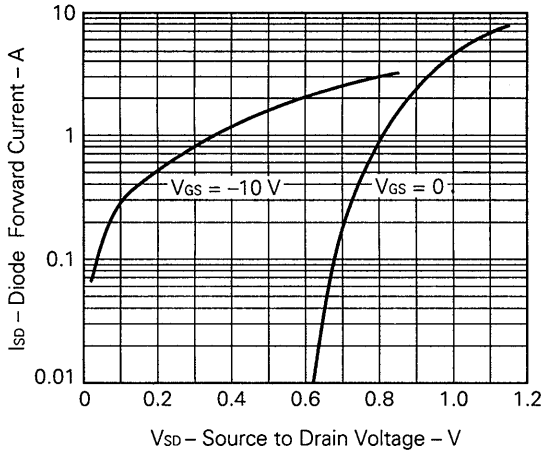

GATE TO SOURCE CUTOFF VOLTAGE vs. CHANNEL TEMPERATURE



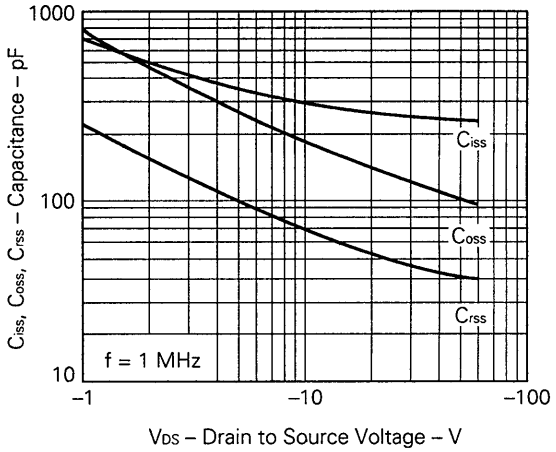

DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



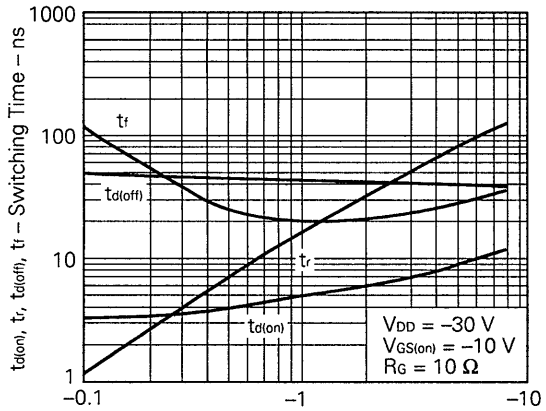
SOURCE TO DRAIN DIODE FORWARD VOLTAGE



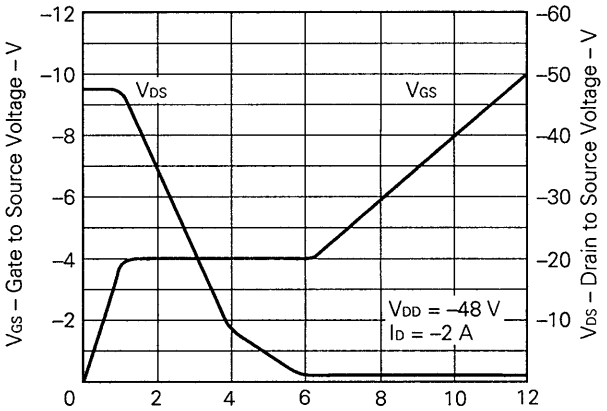

CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



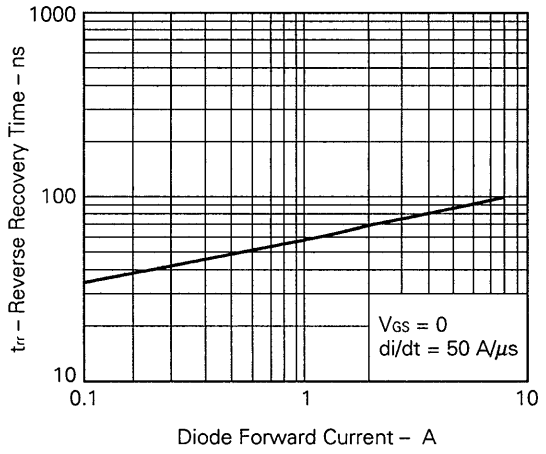

SWITCHING CHARACTERISTICS




DYNAMIC INPUT/OUTPUT CHARACTERISTICS




REVERSE RECOVERY TIME vs. REVERSE DRAIN CURRENT



## Reference

| Application note name | No. |
|---|---|
| Safe operating area of Power MOS FET. | TEA-1034 |
| Application circuit using Power MOS FET. | TEA-1035 |
| Quality control of NEC semiconductors devices. | TEI-1202 |
| Quality control guide of semiconductors devices. | MEI-1202 |
| Assembly manual of semiconductors devices. | IEI-1207 |



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